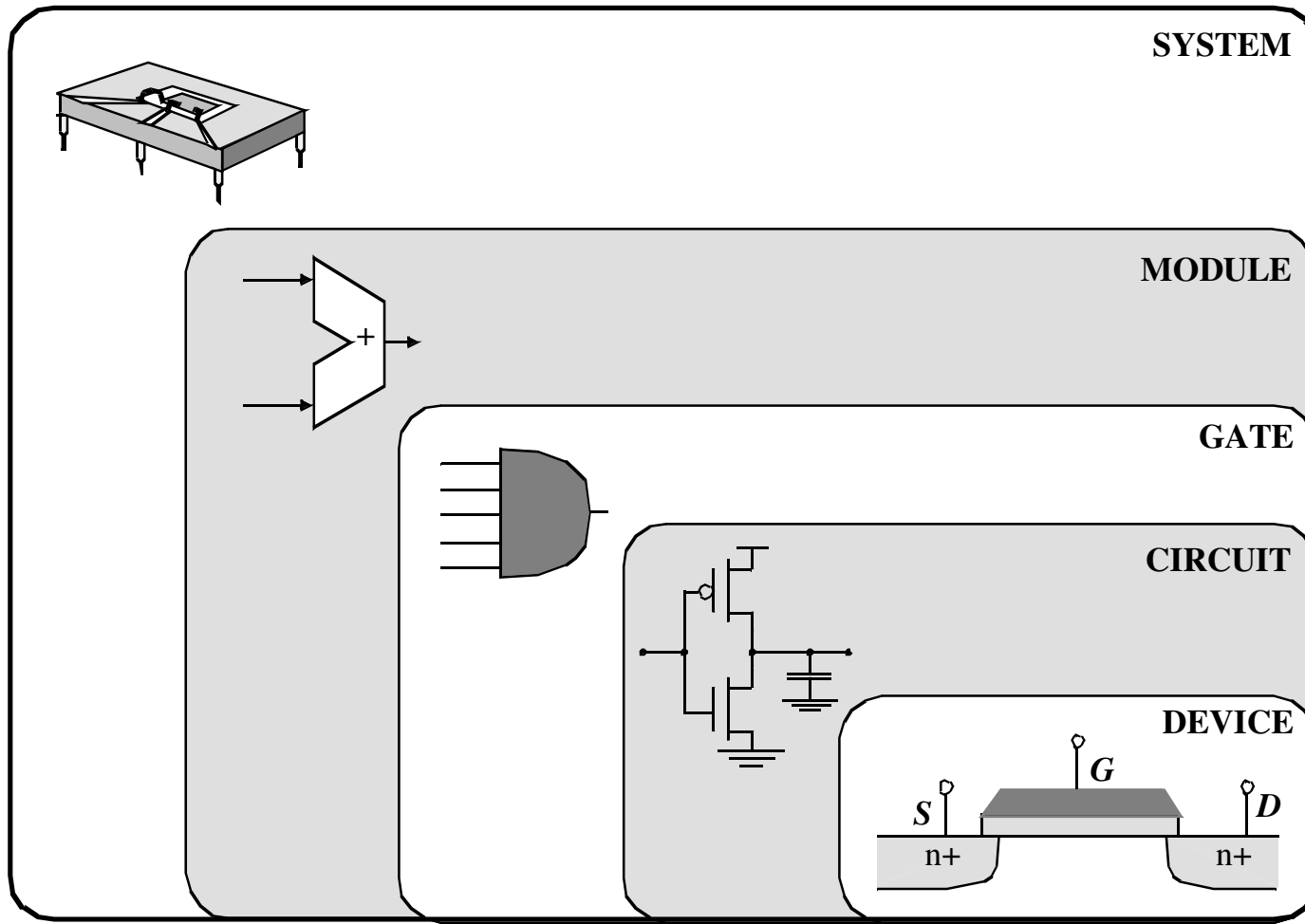
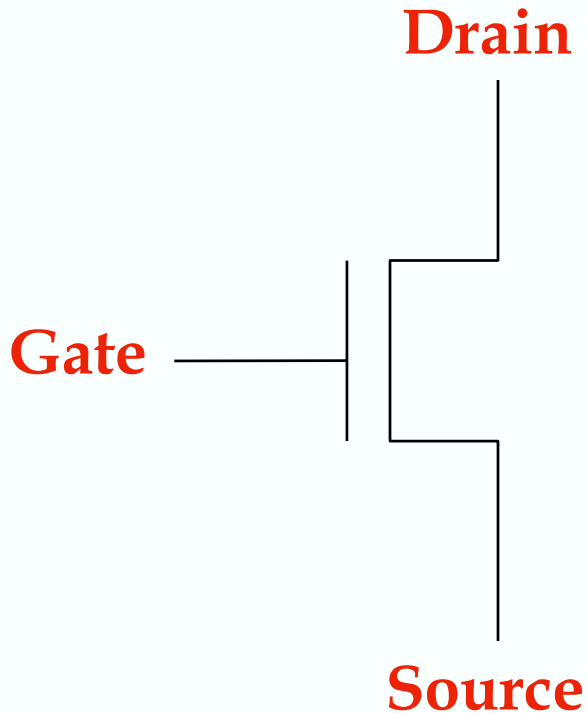


# Design Abstraction Levels

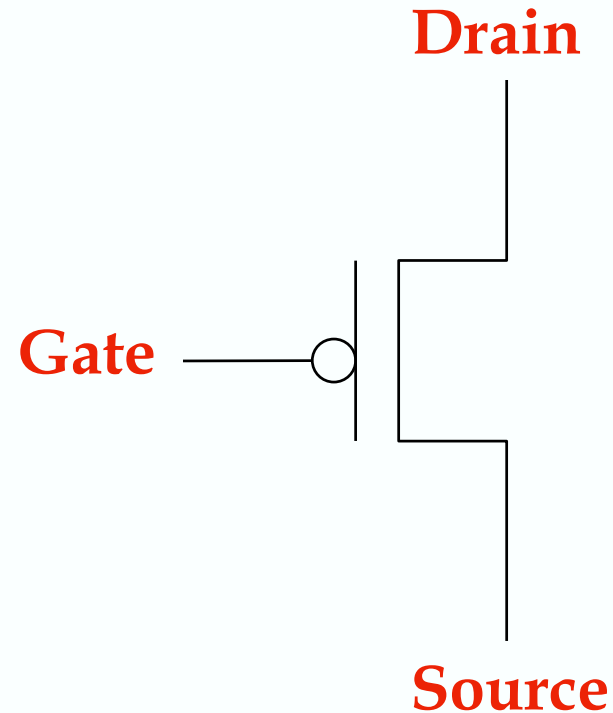


# Complementary Metal-Oxide-Semiconductor (CMOS) Transistors

**NMOS**

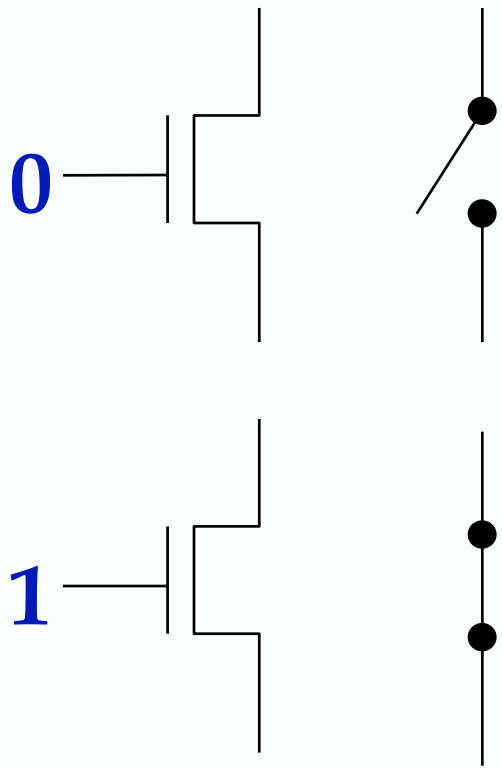


**PMOS**

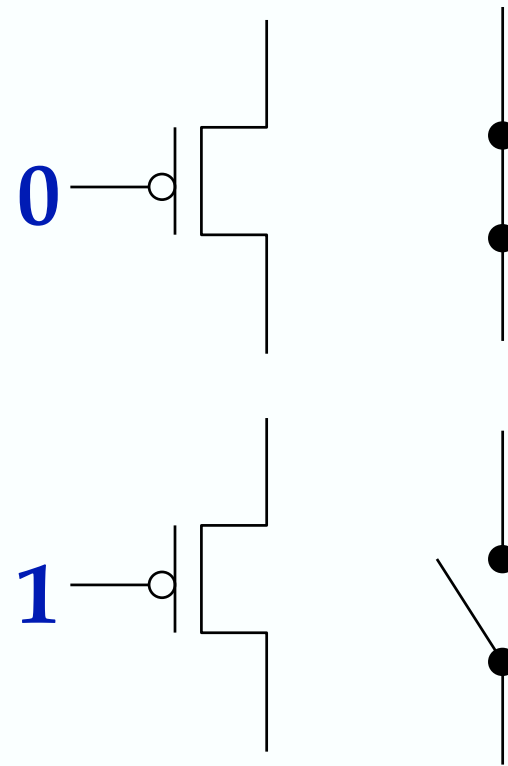


# MOS Transistors as Switches

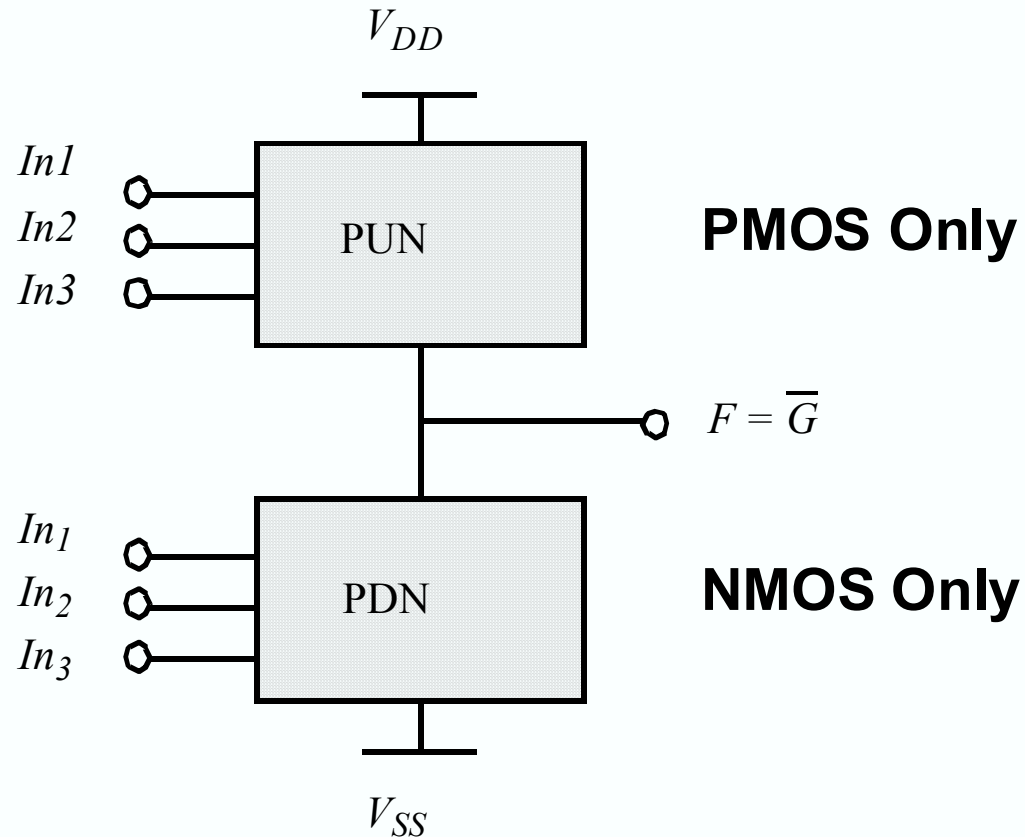
**NMOS**



**PMOS**

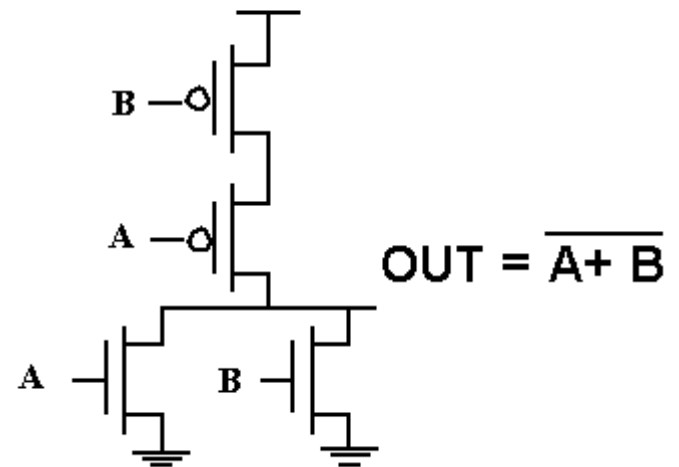
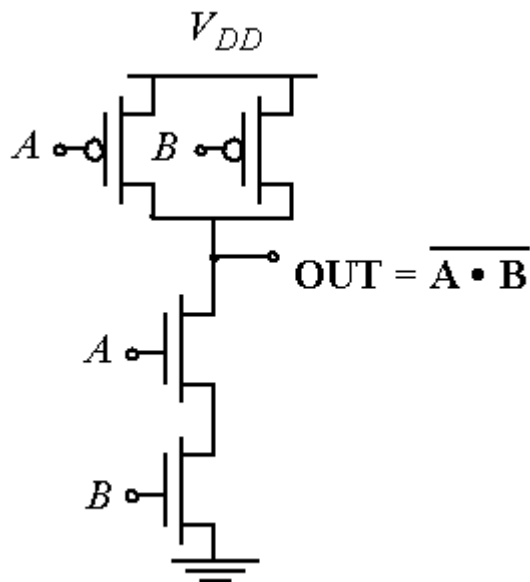
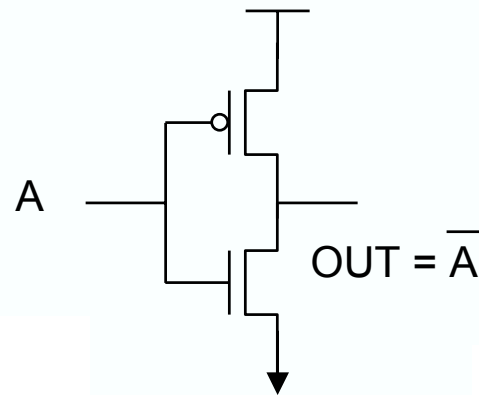


# Static CMOS

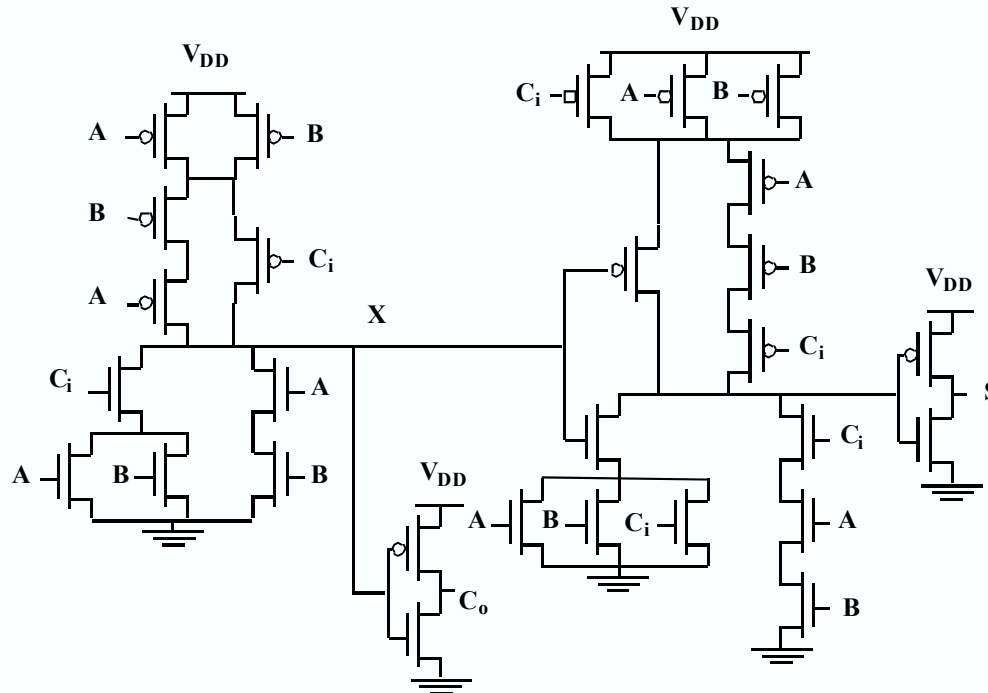


**PUN and PDN are Dual Networks**

# Basic Logic Gates



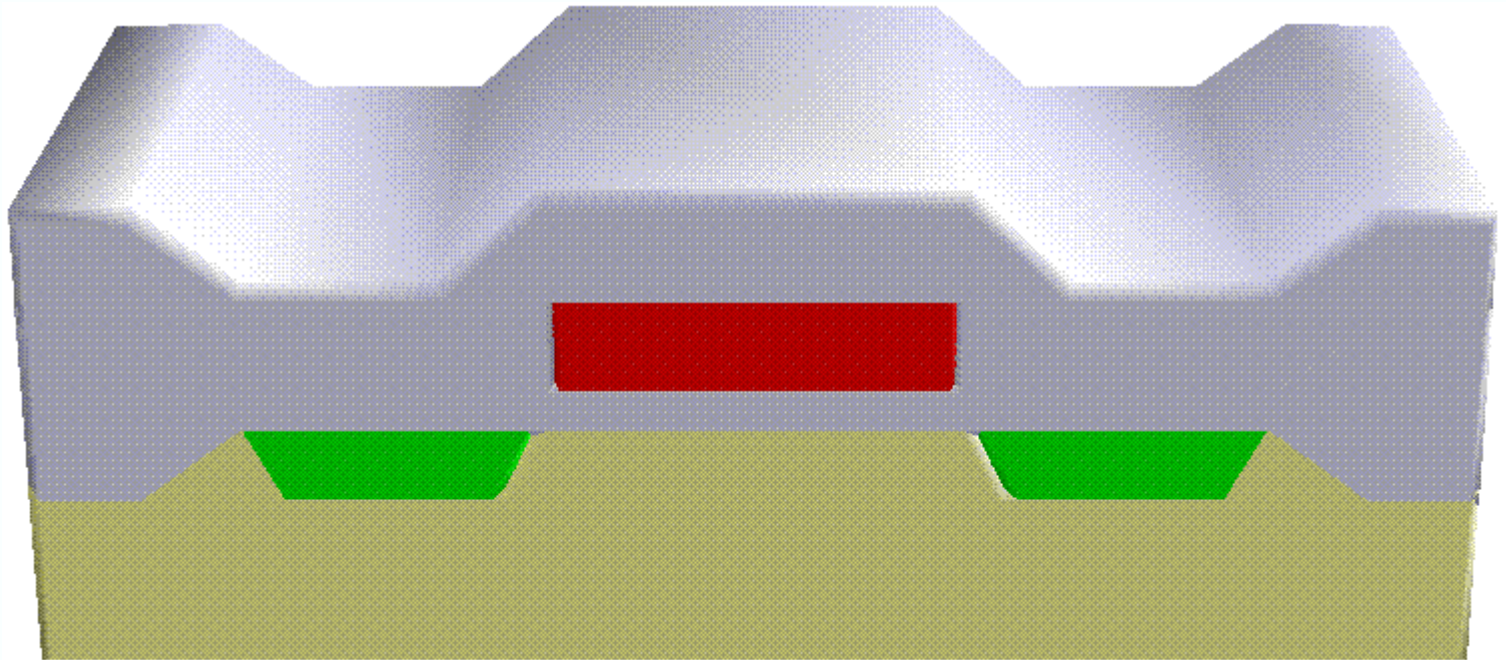
# Example: Full Adder



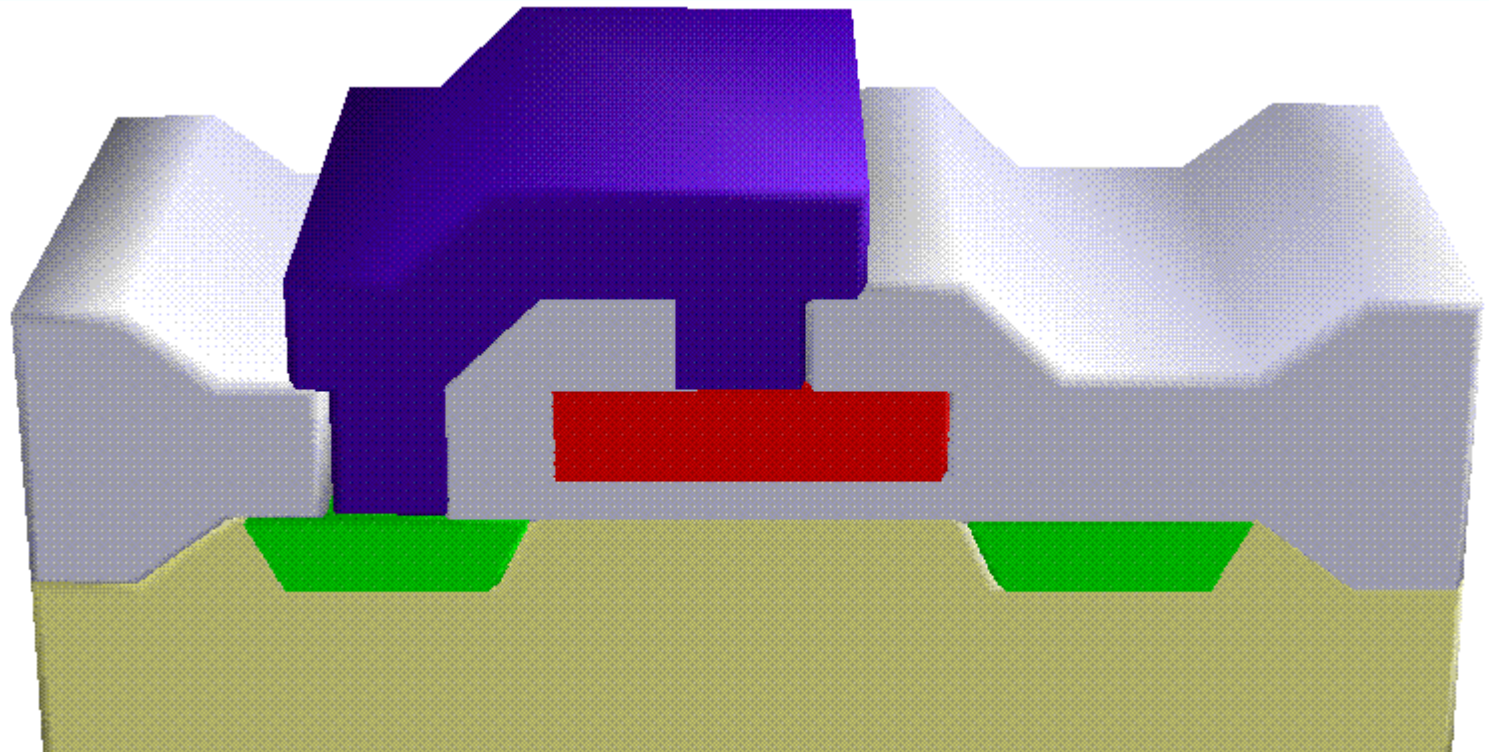
$$C_o = AB + C_i(A+B)$$

28 transistors

# MOSFET

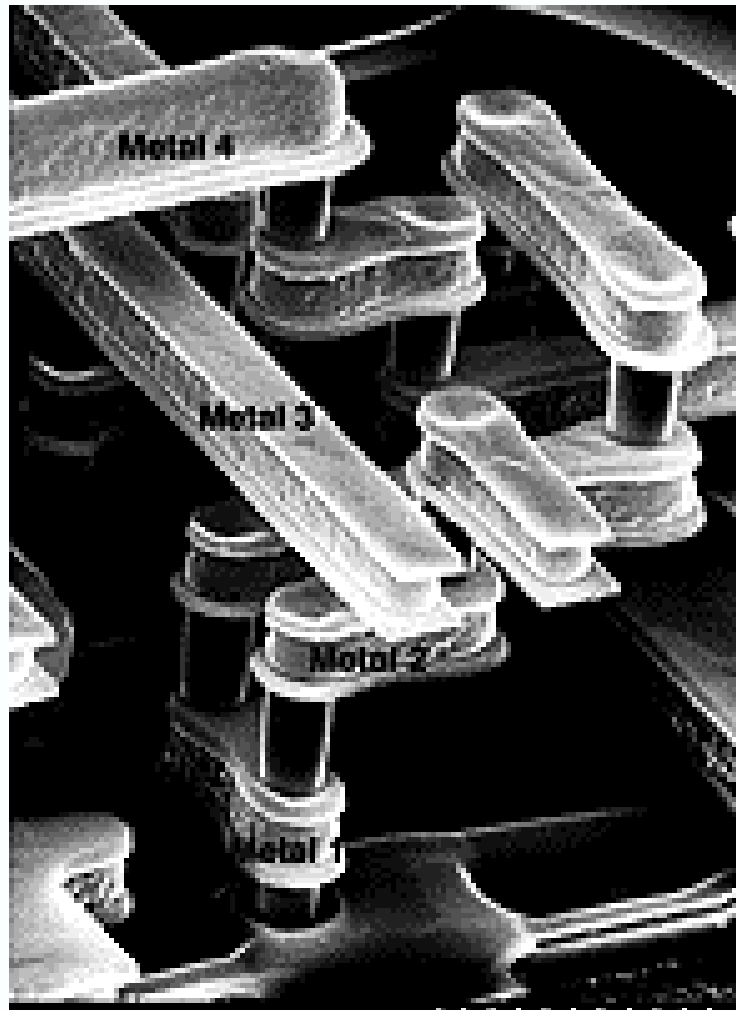


# Metal Interconnect

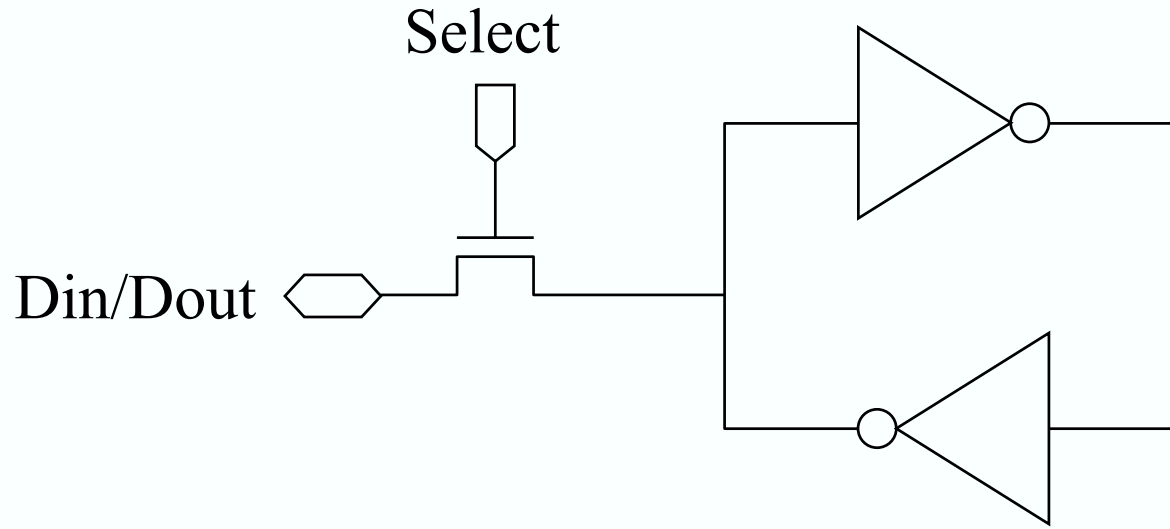




# Modern Interconnect

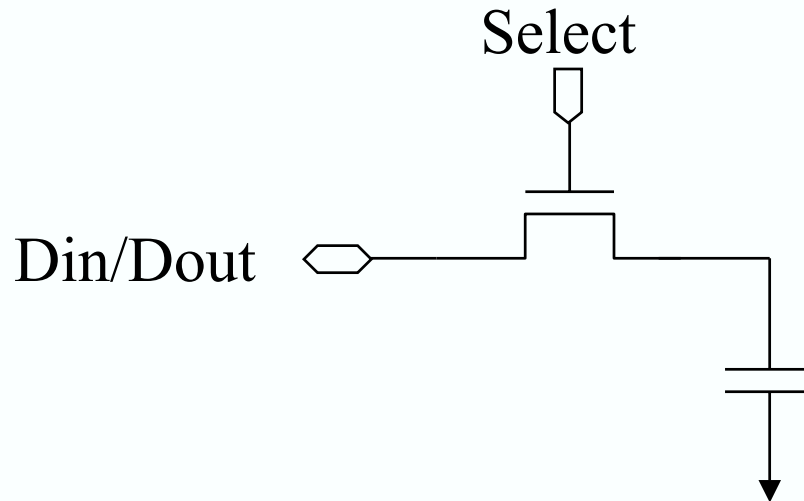


# Feedback-Based Latch



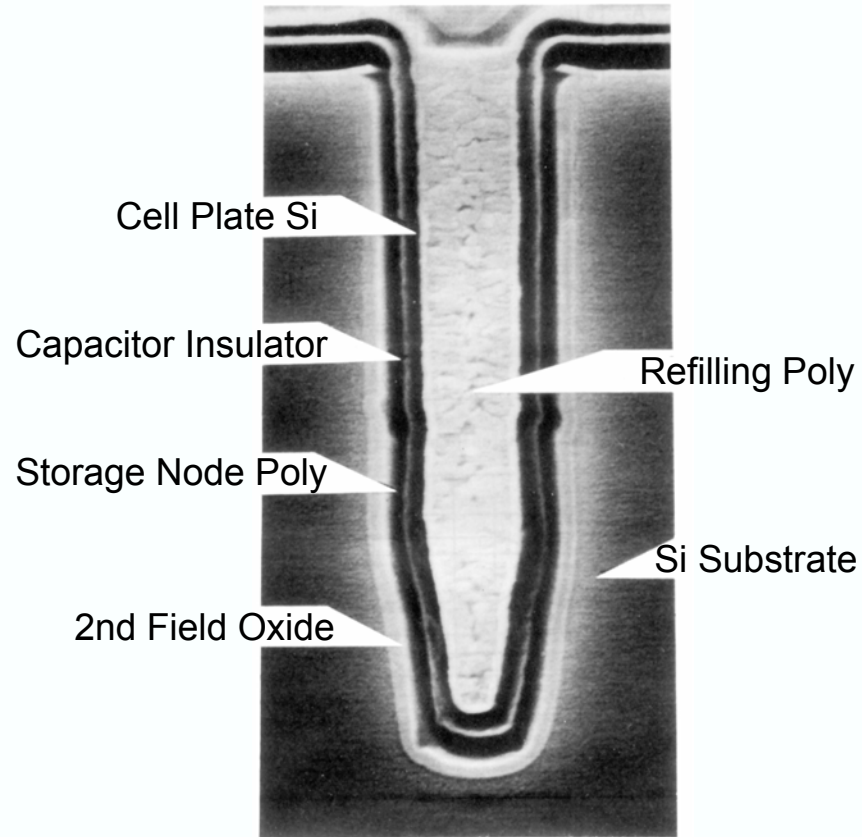
- Pro
  - » Holds data as long as power applied
  - » Actively drives output: can be made fast
- Con
  - » Big (5 transistors in this configuration)

# Charge-Based Latch

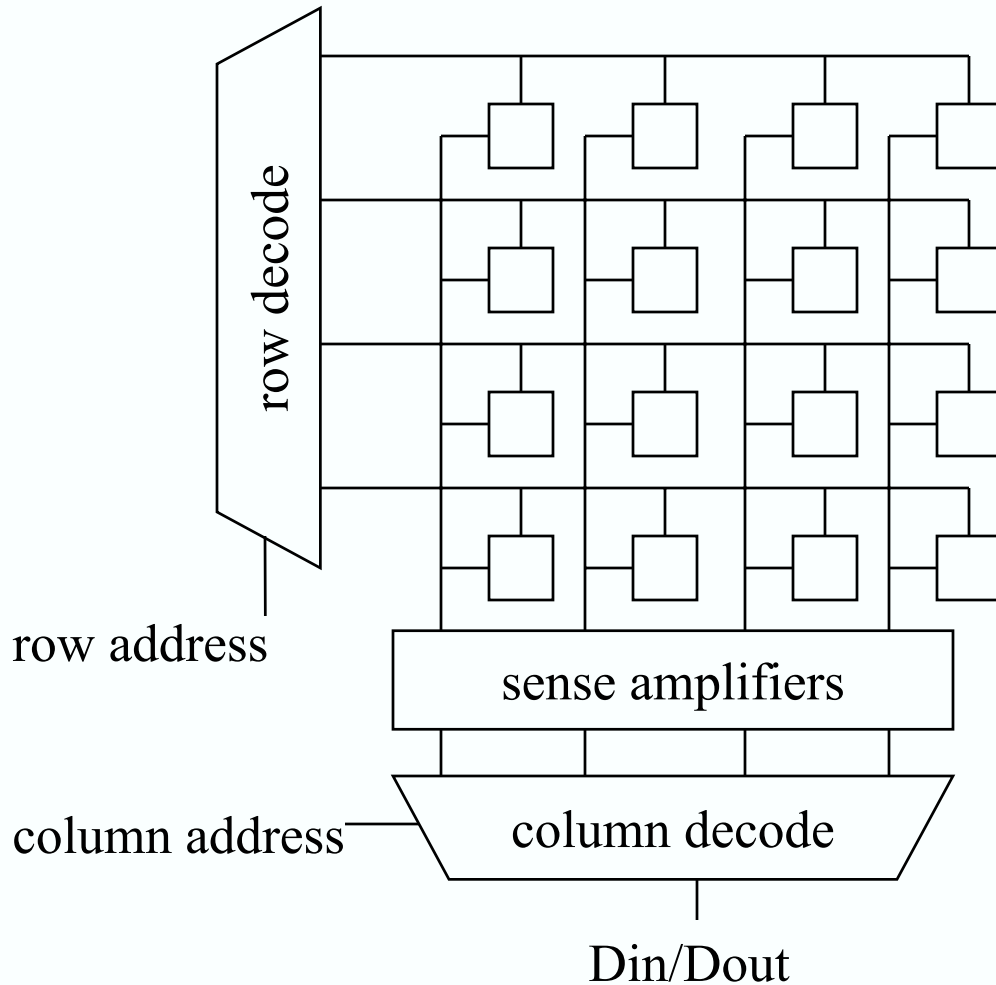


- Pro
  - » Small: 1 transistor, 1 capacitor (may be gate of transistor)
- Con
  - » Charge leaks off capacitor ( $\sim 1$  ms)
  - » Reads can be destructive and slow for large fan-out

# DRAM Trench Capacitor

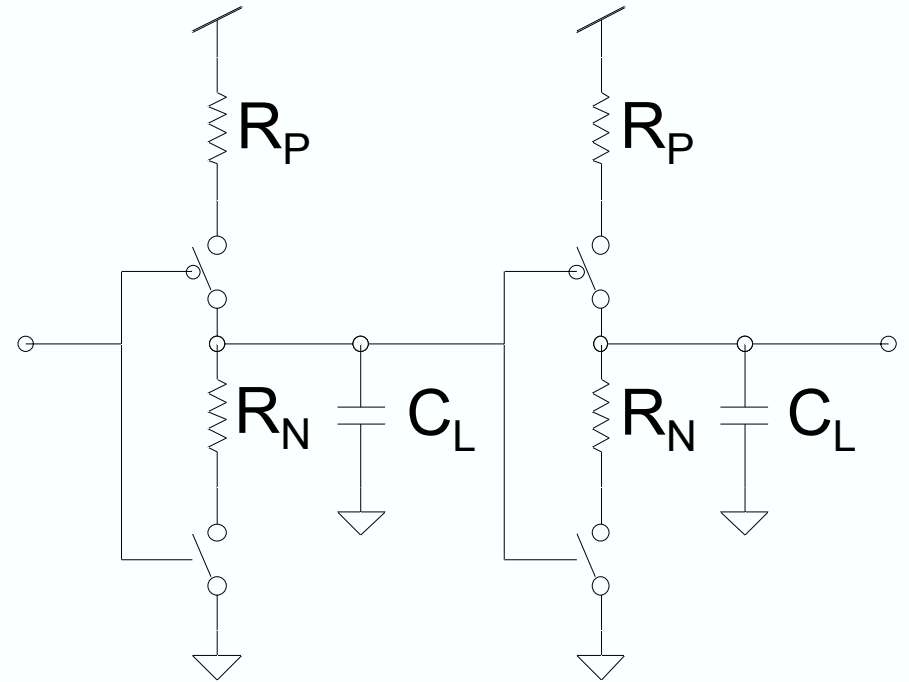
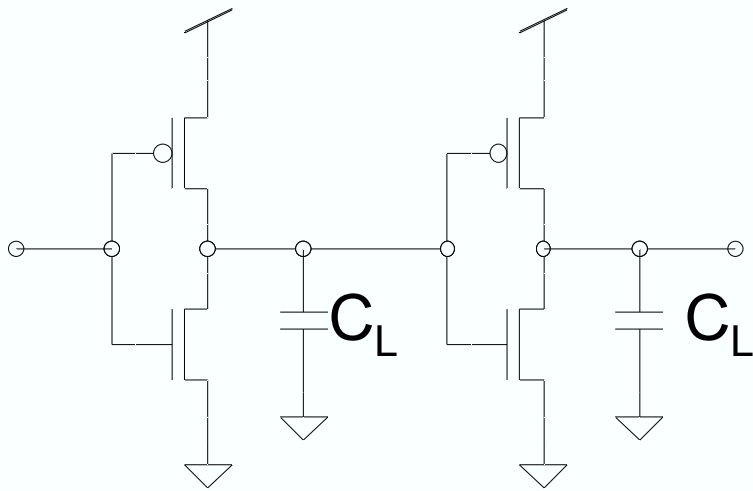


# Array-Structured Memory Architecture



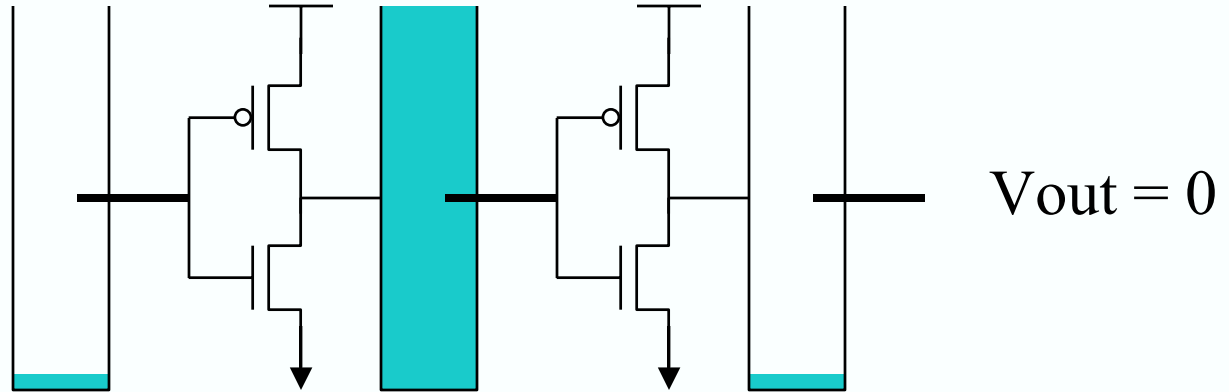
- All cells on selected row sensed simultaneously

# RC Switch Model

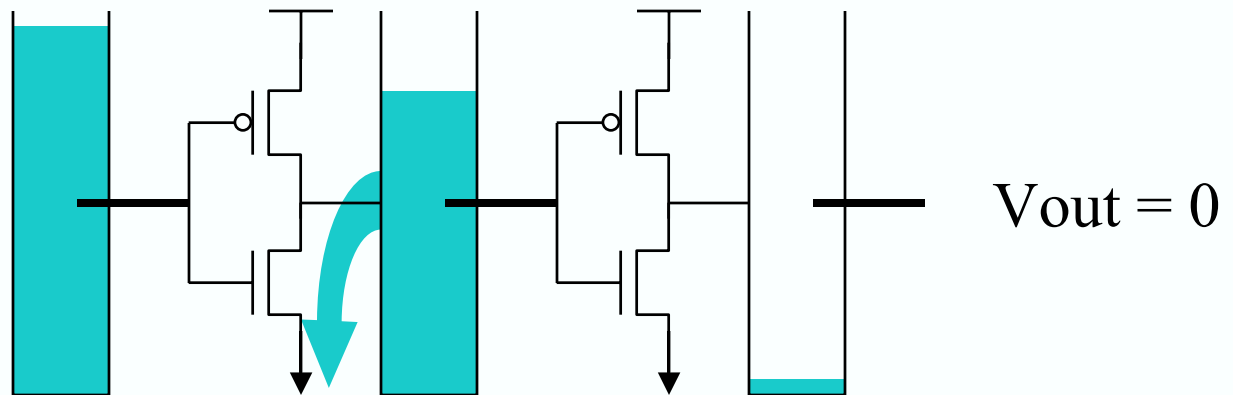


# Signal Propagation (1)

$t < 0$   
 $V_{in} = 0$

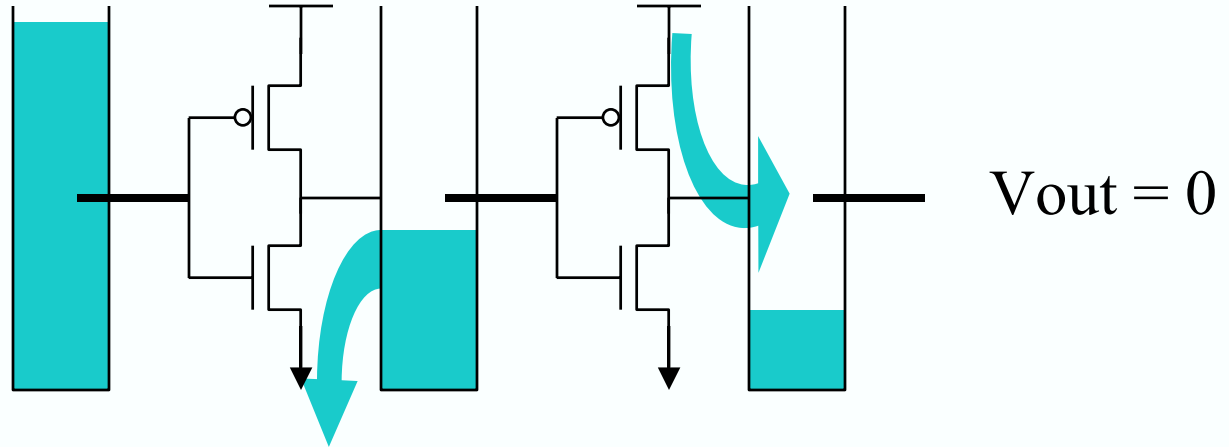


$t = 0$   
 $V_{in} = 1$

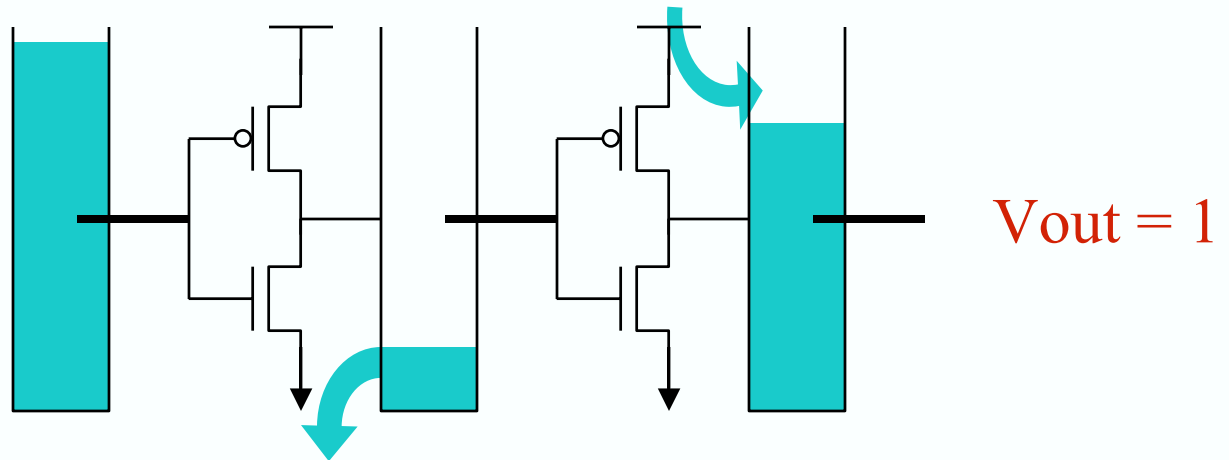


# Signal Propagation (2)

$t = 1$   
 $V_{in} = 0$



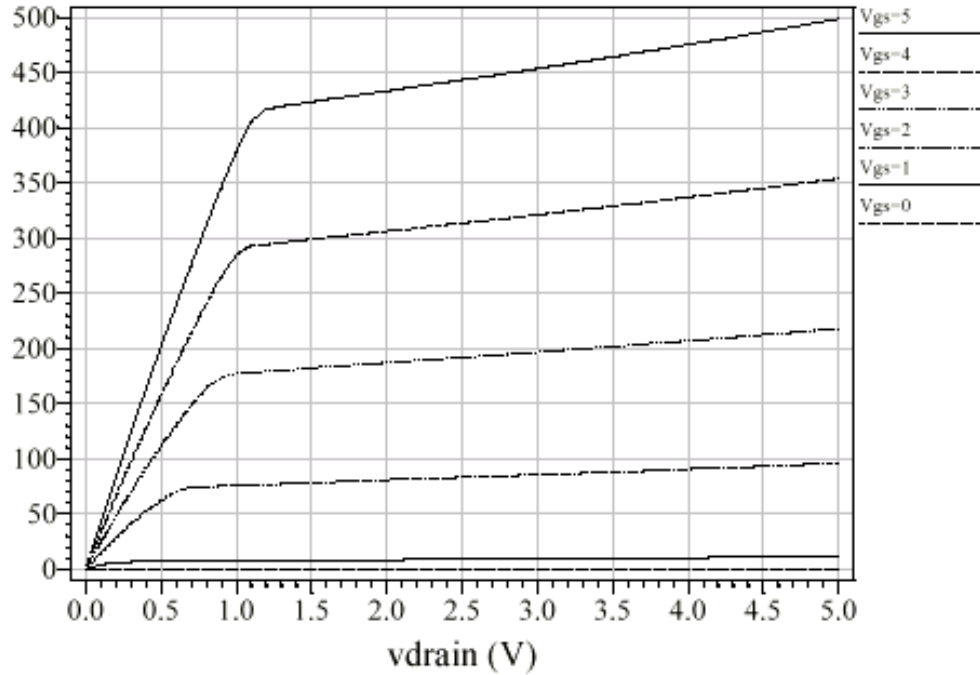
$t = 2$   
 $V_{in} = 1$



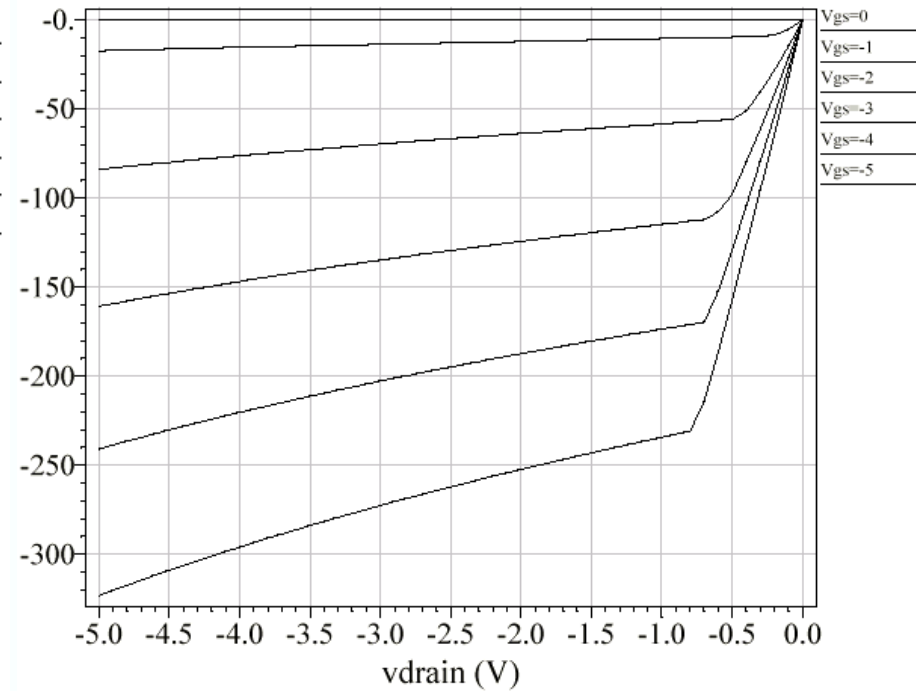


# MOSFET IV Characteristics

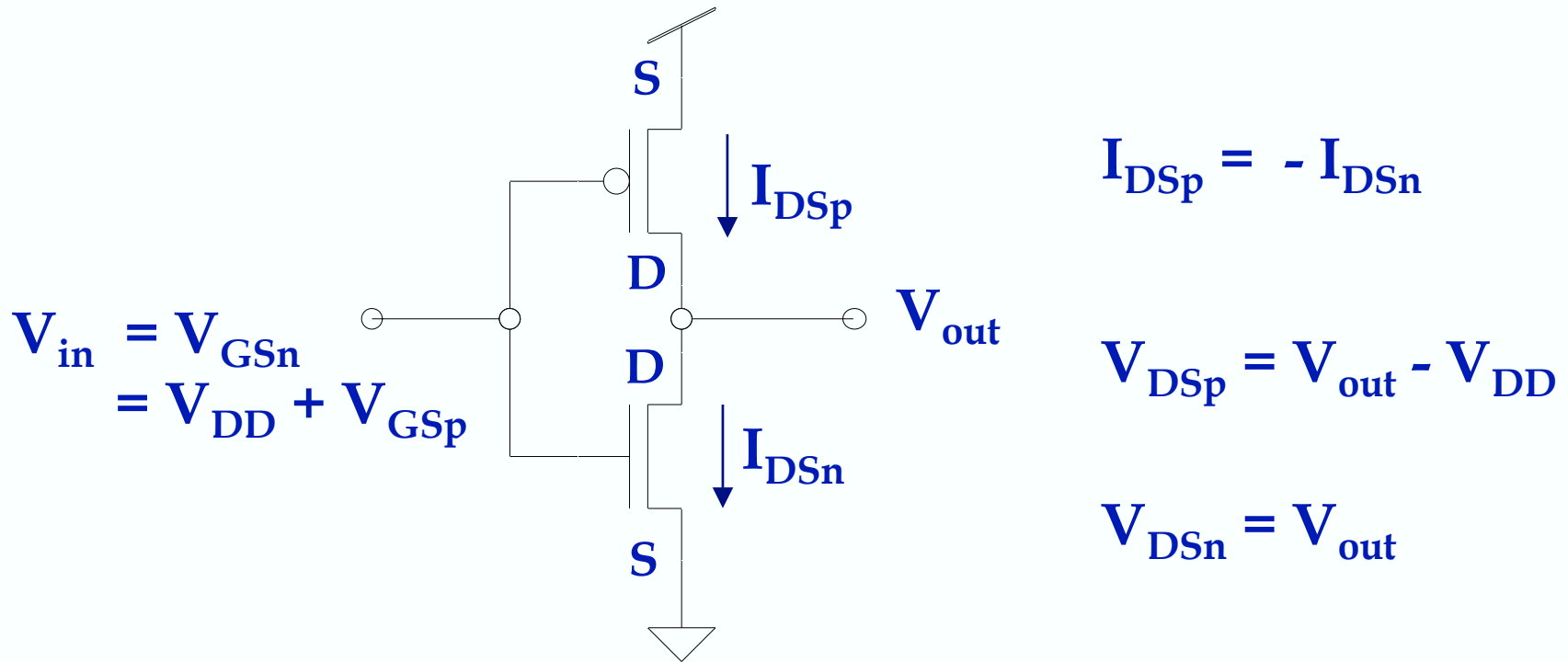
NMOS 1.8/1.2



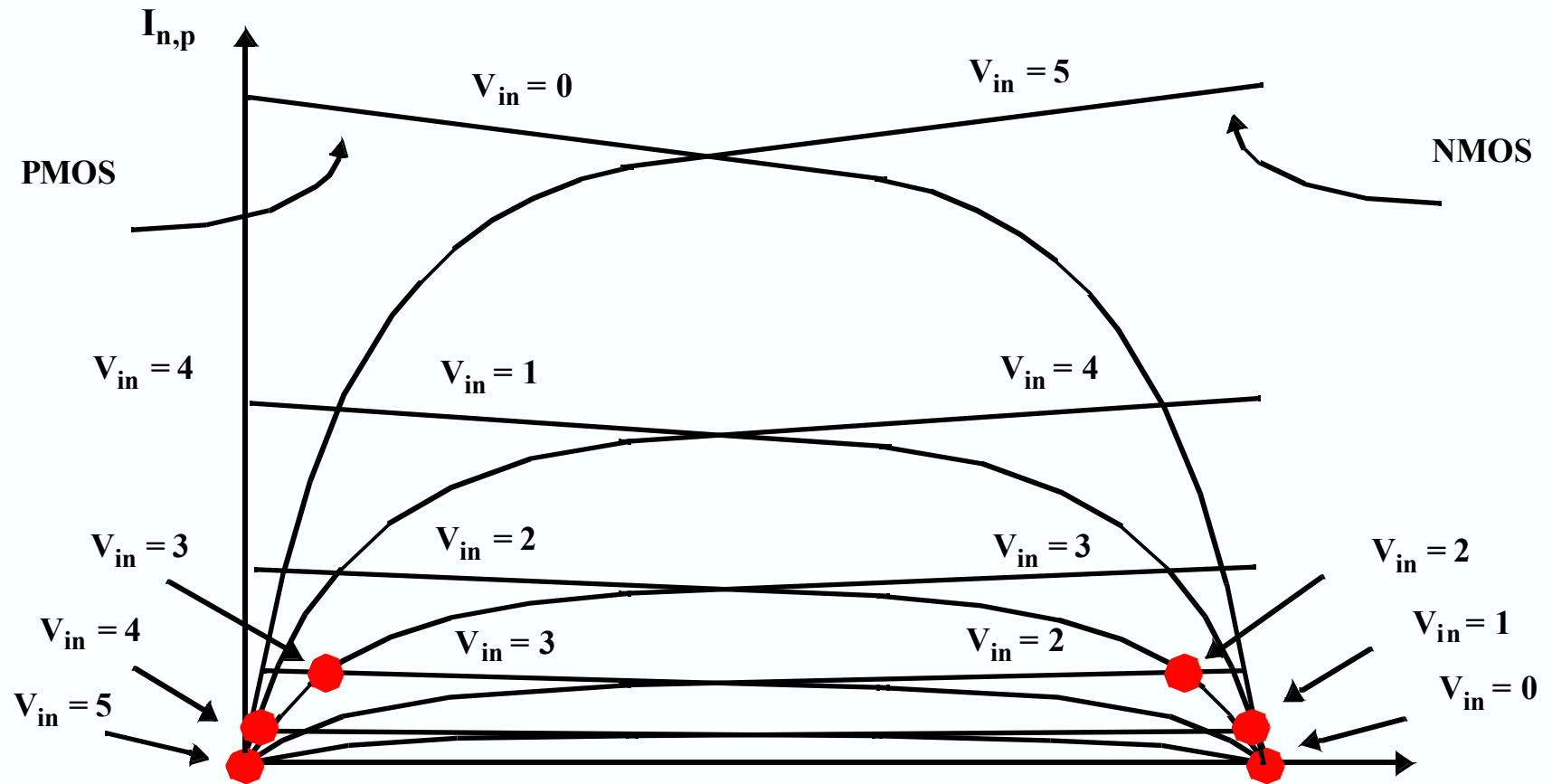
PMOS 5.4/1.2



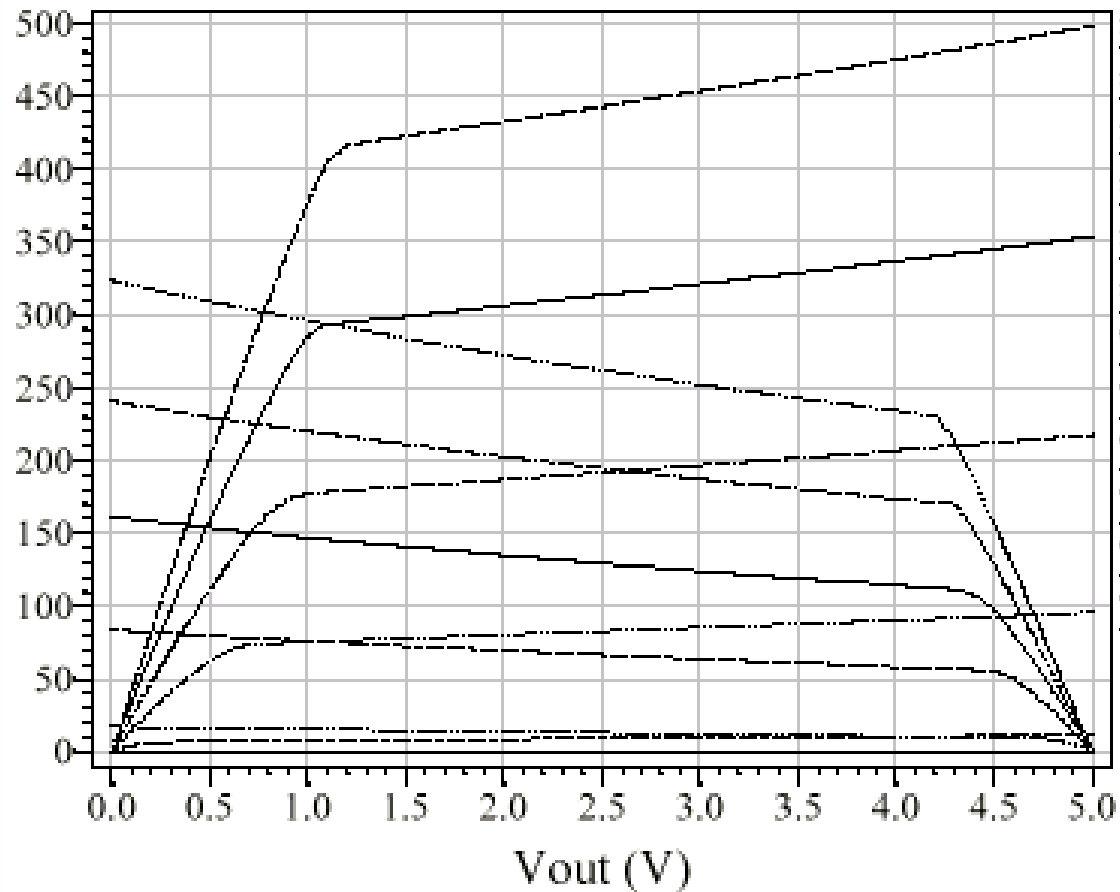
# CMOS Inverter



# CMOS Inverter Load Characteristics

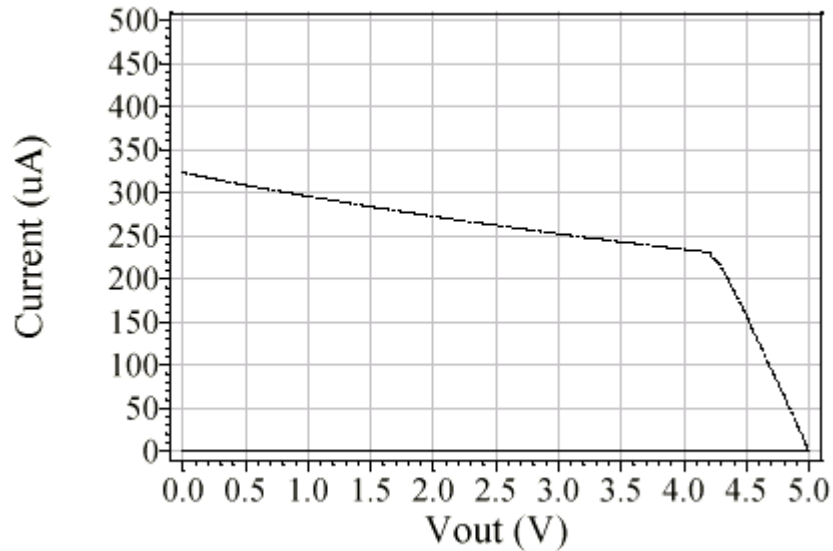


# CMOS “Load Lines”

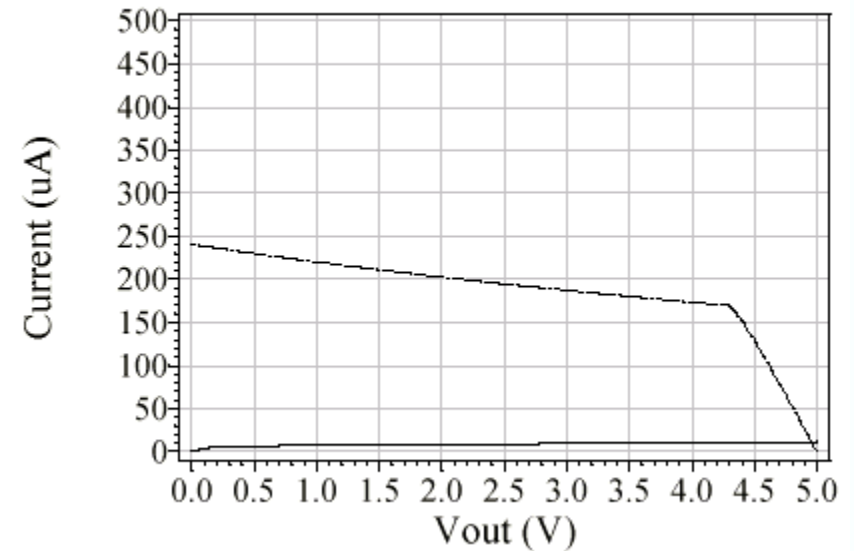


# Finding CMOS VTC--1

$V_{in} = 0$

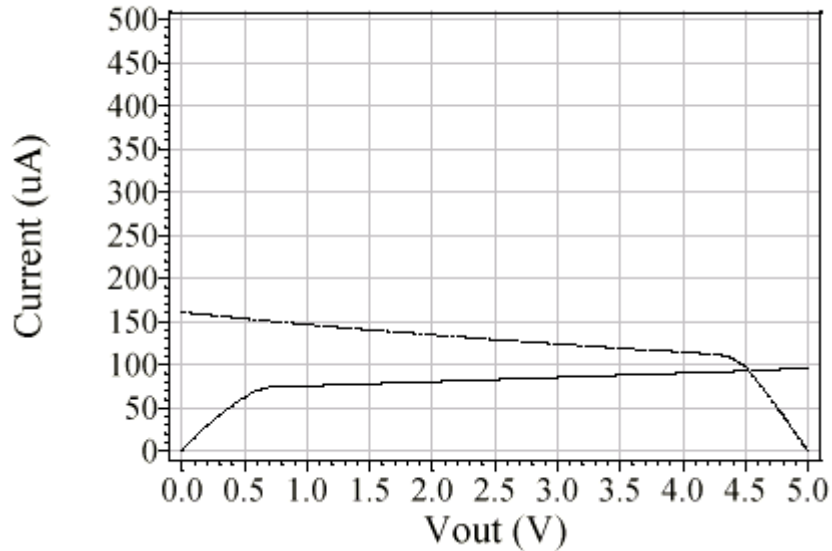


$V_{in} = 1$

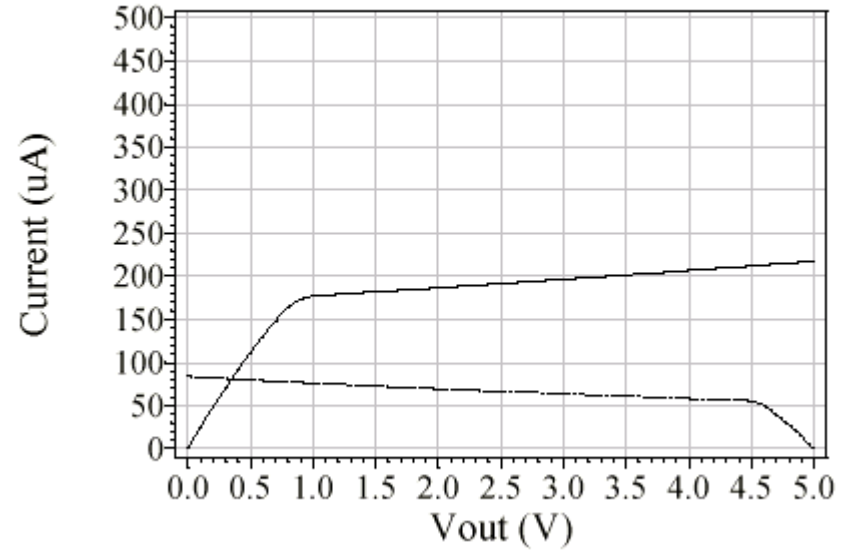


# Finding CMOS VTC--2

$V_{in} = 2$

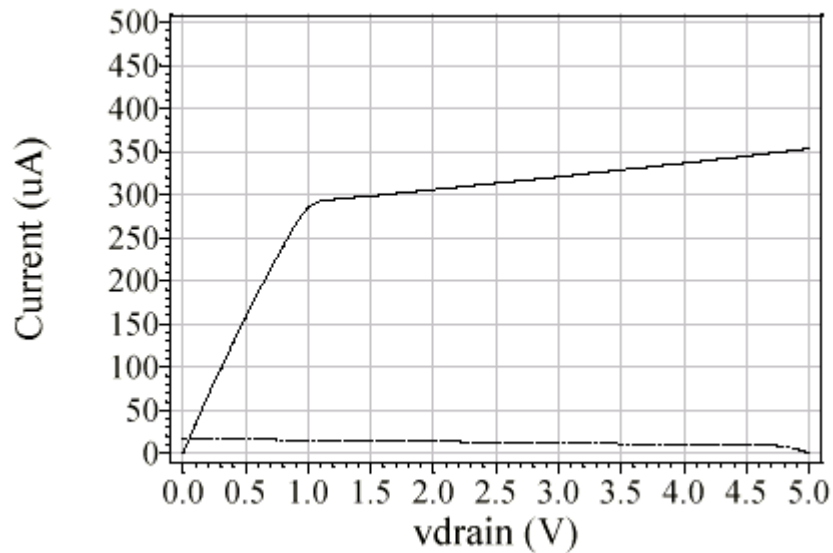


$V_{in} = 3$

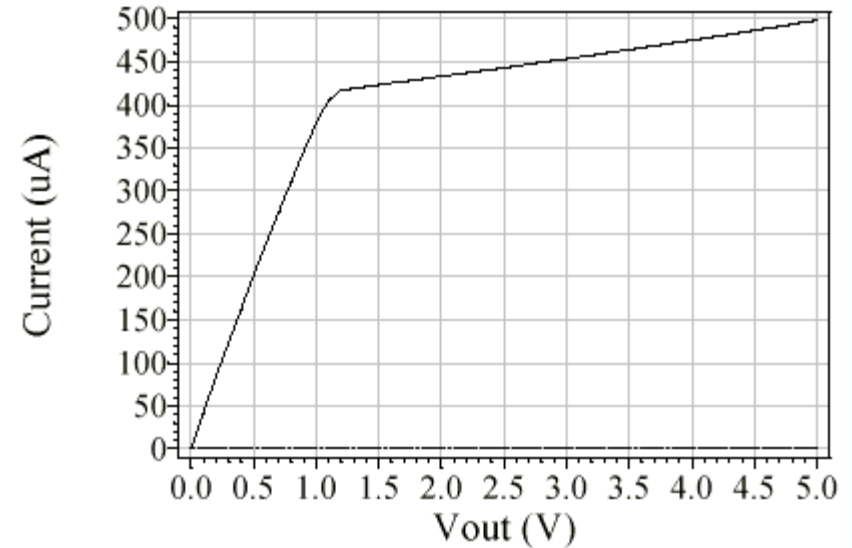


# Finding CMOS VTC--3

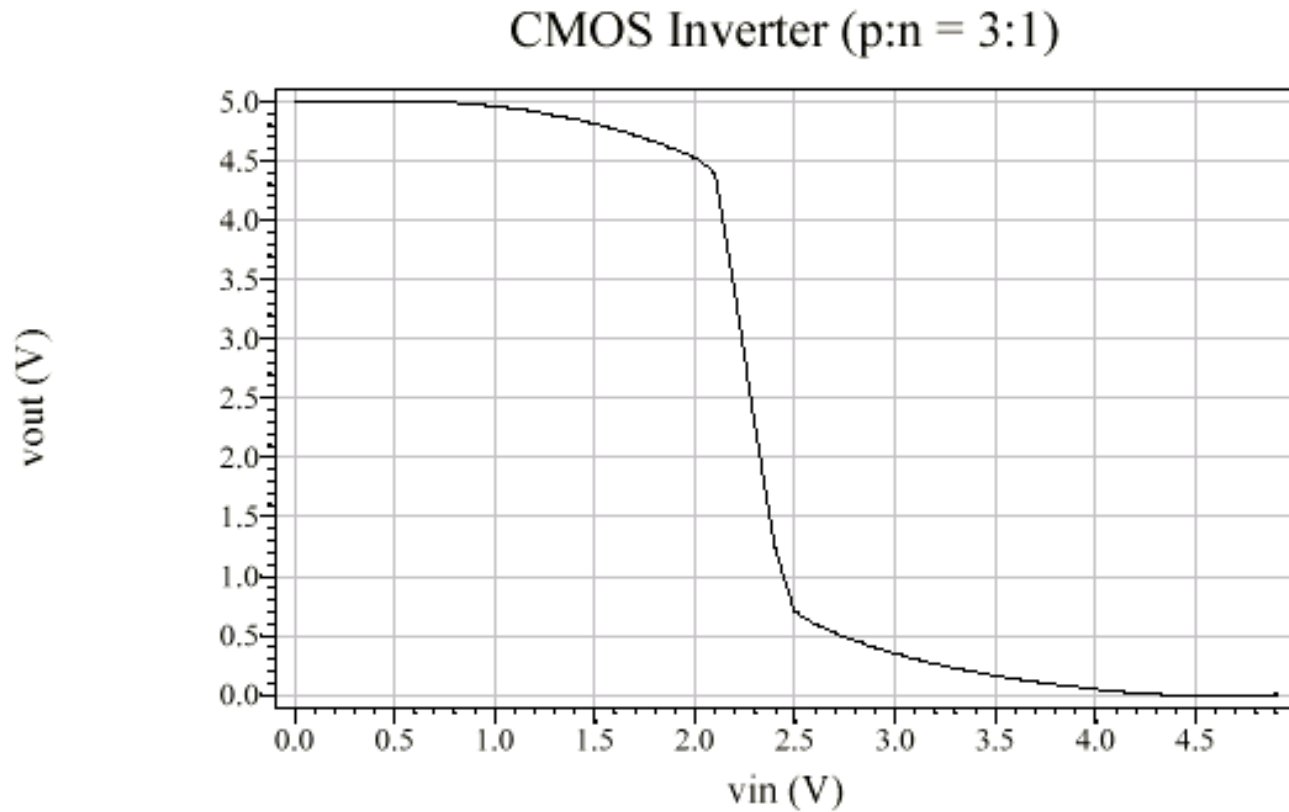
$V_{in} = 4$



$V_{in} = 5$

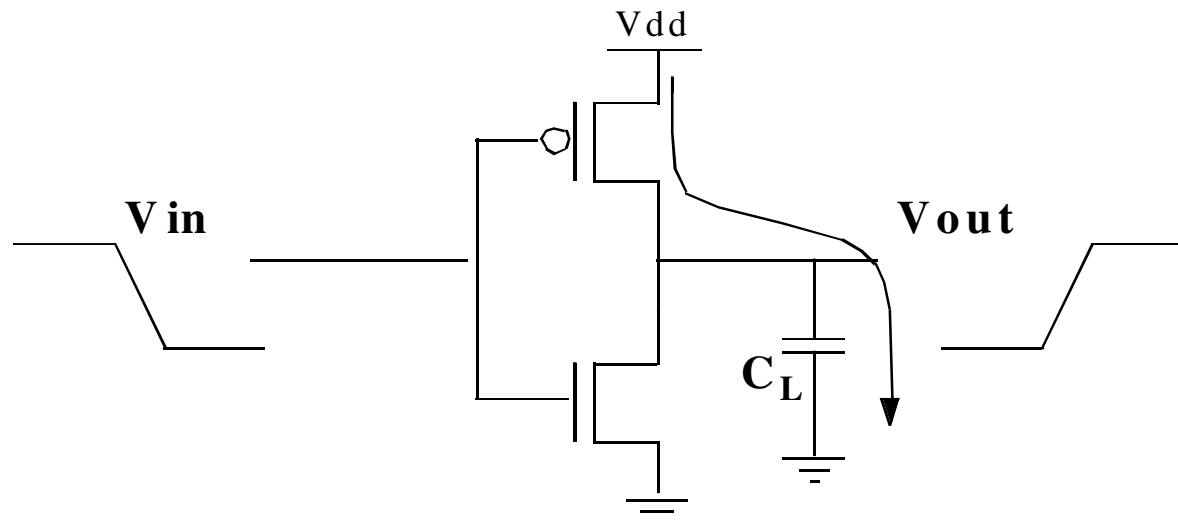


# CMOS VTC--Spice Results





# Dynamic Power Consumption

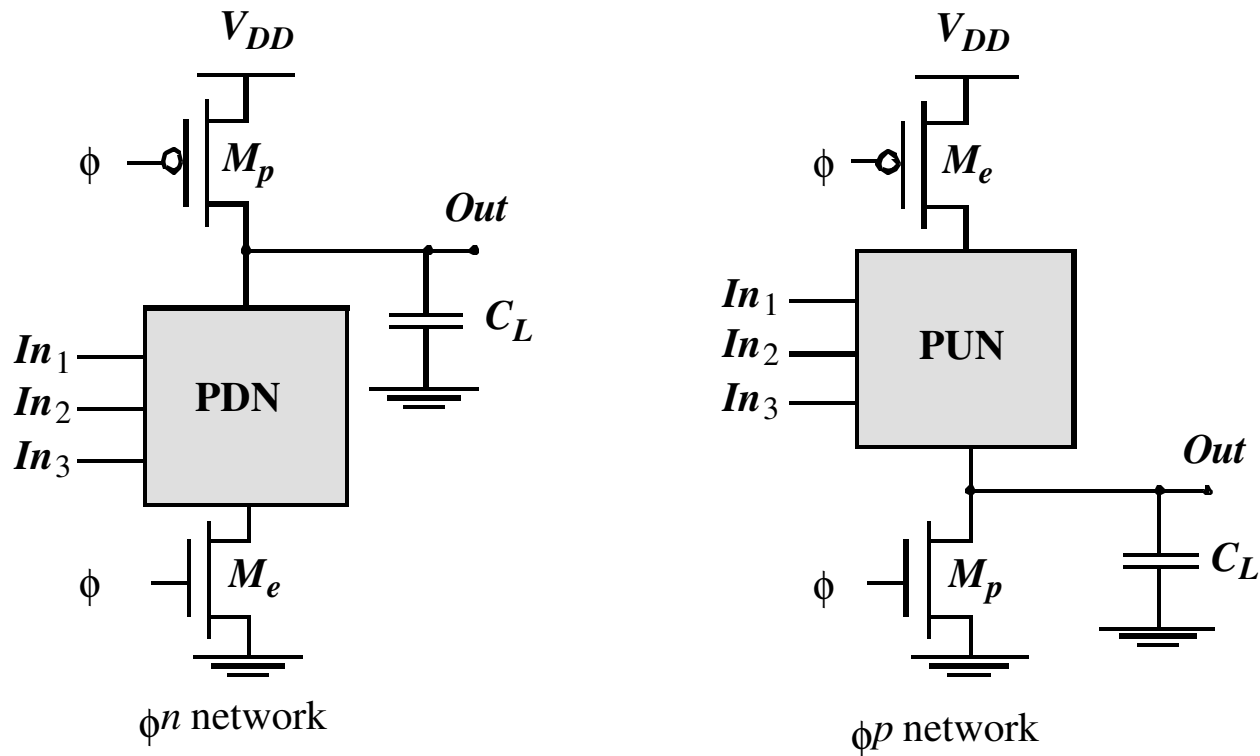


$$\text{Energy/transition} = C_L * V_{dd}^2$$

$$\text{Power} = \text{Energy/transition} * f = C_L * V_{dd}^2 * f$$

- **Not a function of transistor sizes!**
- **Need to reduce  $C_L$ ,  $V_{dd}$ , and  $f$  to reduce power.**

# Dynamic Logic



2 phase operation:

- Precharge
- Evaluation